

Ultra 1.24V Precision Adjustable Shunt Regulator

FEATURES

- Low Voltage Operation..... 1.24V
- Trimmed Bandgap to..... 0.5% / 1%
- Wide Operating Current 100 μ A to 100mA
- Extended Temperature Range..... 0°C to 105°C
- Adjustable Output Voltage..... V_{REF} to 18V
- Low Temperature Coefficient..... 50 ppm/°C
- Offered in TO-92, SOIC, SOT-89, SOT-23-3

APPLICATIONS

- 3.0V to 3.3V Switching Power Supplies
- Adjustable Supplies
- Error Amplifiers
- Single Supply Amplifier
- Monitors / VCR / TV
- Personal Computers

PRODUCT DESCRIPTION

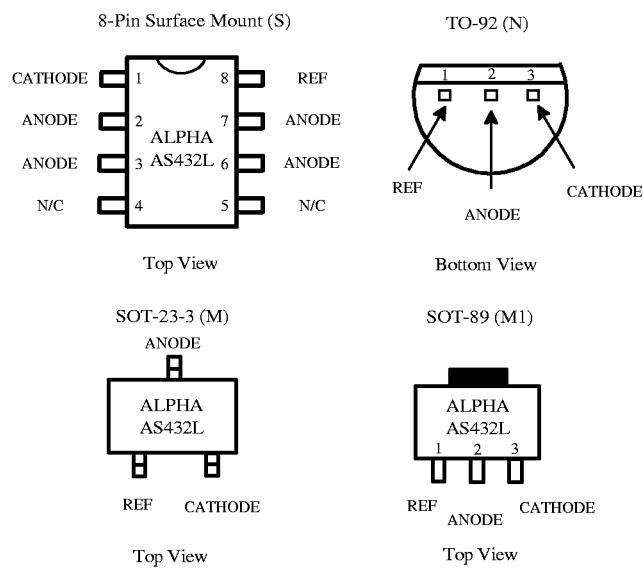
The ALPHA Semiconductor's AS432L is a 3-terminal Adjustable Shunt Voltage Regulator providing a highly accurate 1.24V bandgap reference with 0.5% tolerance. The AS432L thermal stability, wide operating current (100mA) and temperature range (0°C to 105°C) makes it suitable for broad range of applications. AS432L tolerance of 0.5% is proven to be sufficient to overcome other errors in the system to virtually eliminate the need for trimming in the power supply manufactures assembly line and contribute a significant cost savings.

The AS432L is an ideal voltage reference in an isolated feedback circuit for 3.0V to 3.3V switching mode power supplies. AS432L offers many advantages over TLV431, such as, wider output voltage up to 18V vs. 6V, output current of 80mA vs. 15mA, and a wider temperature range with tighter tolerance down to 0.5%. ALPHA Semiconductor, is the only manufacture to offer the AS432L equivalent in SOT-23-3 with all above advantages.

ORDERING INFORMATION

Part Number	Tolerance	Package Type
AS432LAN	0.5%	TO-92
AS432LAM1	0.5%	SOT-89
AS432LAS	0.5%	SO-8
AS432LAM	0.5%	SOT-23-3
AS432LN	1%	TO-92
AS432LM1	1%	SOT-89
AS432LS	1%	SO-8
AS432LM	1%	SOT-23-3

PIN CONNECTIONS

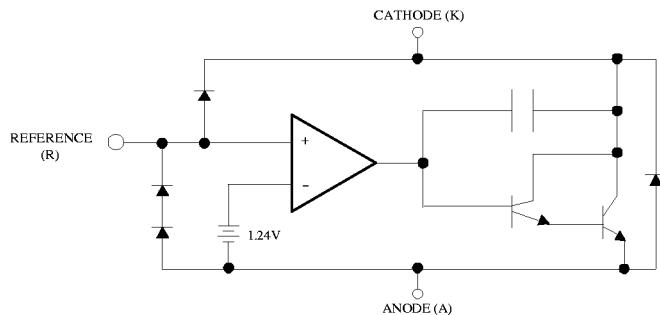


MARKING INFORMATION

[For SOT-23 (3 and 5 Pin) and SOT-89 only]

Device	Marking
AS432LA	BAXX
AS432L	BBXX

XX is lot number assigned by production

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Rating	Units
Cathode-Anode Reverse Breakdown	V_{DA}	18	V
Anode-Cathode Forward Current	I_{AK}	1	A
Operating Cathode Current	I_{KA}	100	mA
Reference Input Current	I_{REF}	1	mA
Continuous Power at 25°C	P_D		
TO-92		775	mW
8L SOIC		750	mW
SOT-89		1000	mW
SOT-23		200	mW
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	- 65 to +150	°C
Lead Temperature (Soldering 10 sec.)	T_L	300	°C

Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED CONDITIONS

Parameter	Symbol	Rating	Unit
Cathode Voltage	V_{KA}	V_{REF} to 18	V
Cathode Current	I_K	500	μ A

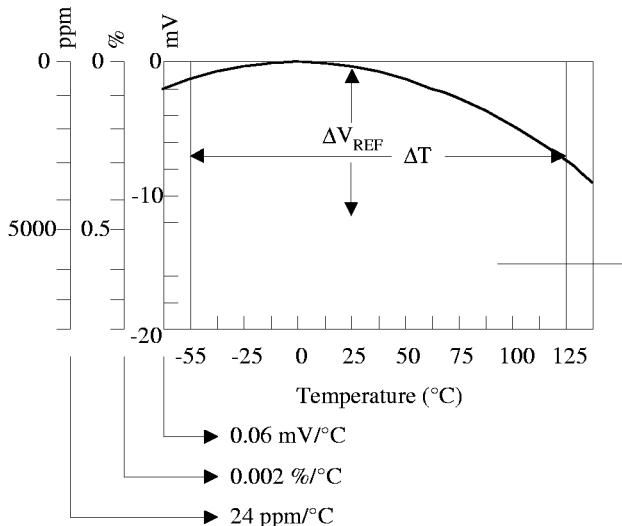
TYPICAL THERMAL RESISTANCES

Package	θ_{JA}	θ_{JC}	Typical Derating
TO-92	160 °C/W	80 °C/W	6.3 mW/°C
SOIC	175 °C/W	45 °C/W	5.7 mW/°C
SOT-89	110 °C/W	8 °C/W	9.1 mW/°C
SOT-23	575 °C/W	150 °C/W	1.7 mW/°C

ELECTRICAL CHARACTERISTICS are guaranteed over the full junction temperature range (0°C to 105°C). Ambient temperature must be derated based upon power dissipation and package thermal characteristics. Unless otherwise specified, test conditions are: $V_{KA} = V_{REF}$ and $I_K = 10\text{mA}$.

Parameter	Symbol	Test Circuit	Test Condition	AS432AL			AS432L			Unit
				Min	Typ	Max	Min	Typ	Max	
Output Voltage	V_{REF}	1 1	$I_K = 500\mu\text{A}$, $T_J = 25^\circ\text{C}$, $V_K = V_{REF}$	1.2338	1.240	1.2462	1.2276	1.240	1.2524	V
Line Regulation	V_{REF}	1	$V_{KA} = 1.25\text{V}$ to 15V		10	30		10	30	mV
Load Regulation	V_{REF}	1	$I_K = 100\mu\text{A}$ to 80mA		10			3		mV
Temperature Deviation	V_{REF}	1	$0 < T_J < 105^\circ\text{C}$		2	6		2	6	mV
Reference Input Current	I_{REF}	2			3	6		3	6	μA
Reference Input Current Temperature Coefficient	I_{REF}	2	$0 < T_J < 105^\circ\text{C}$		0.3	0.6		0.3	0.6	μA
Minimum Cathode Current for Regulation	$I_K(\text{MIN})$	1			80	100		80	100	nA
Off State Leakage	$I_K(\text{MIN})$	3	$V_{REF} = 0\text{V}$, $V_{KA} = 18\text{V}$		0.04	500		0.04	500	nA

Calculating Average Temperature Coefficient (TC)



- TC in $\text{mV}/^\circ\text{C} = \frac{\Delta V_{REF} (\text{mV})}{\Delta T_A}$
- TC in $\%/\text{ }^\circ\text{C} = \left(\frac{\Delta V_{REF}}{V_{REF} \text{ at } 25^\circ\text{C}} \right) \times 100$
- TC in $\text{ppm}/^\circ\text{C} = \left(\frac{\Delta V_{REF}}{V_{REF} \text{ at } 25^\circ\text{C}} \right) \times 10^6$

TEST CIRCUITS

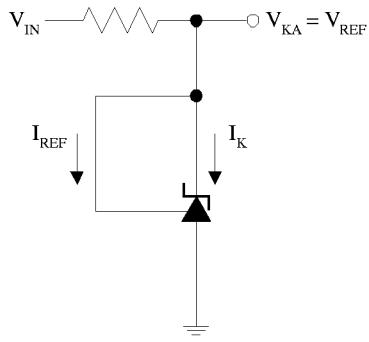


Figure 1a. Test Circuit 1

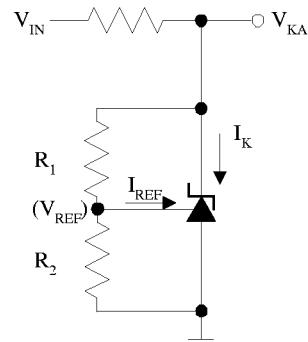


Figure 1b. Test Circuit 2

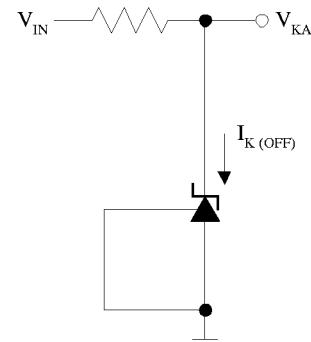
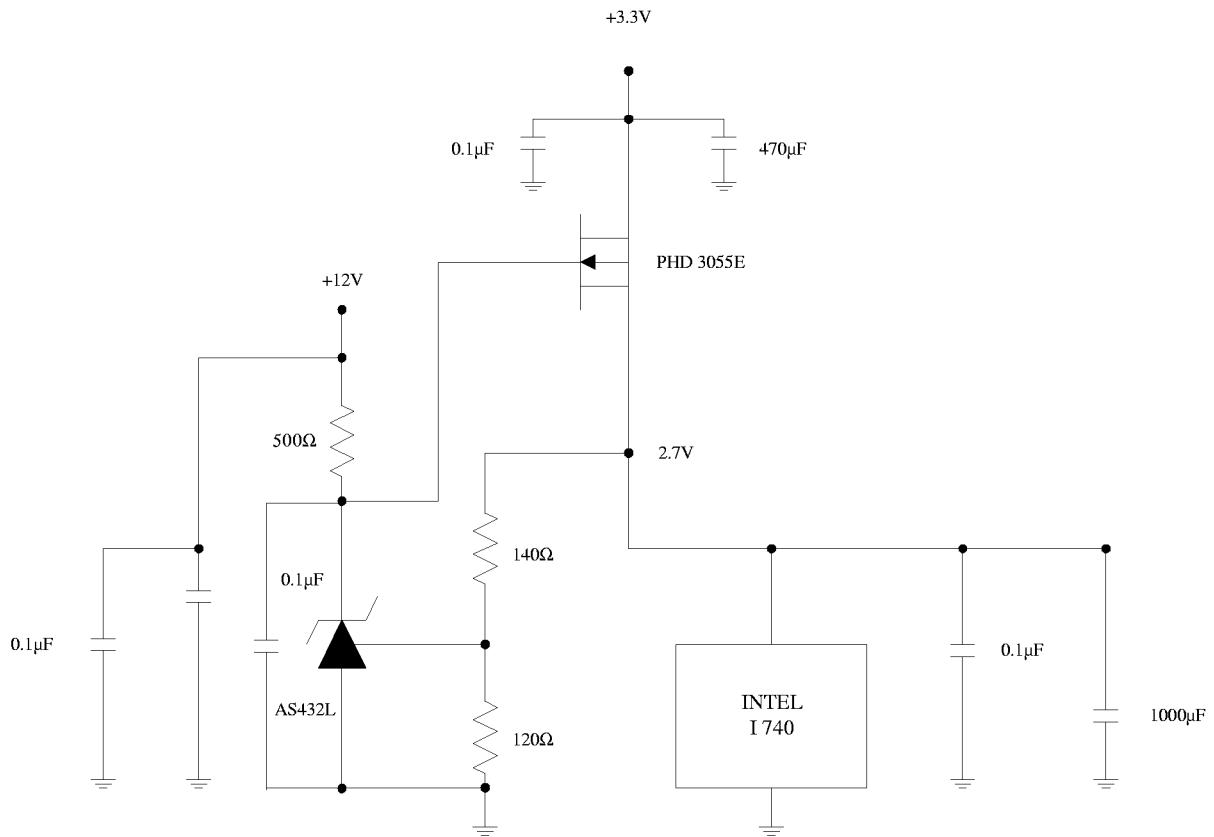


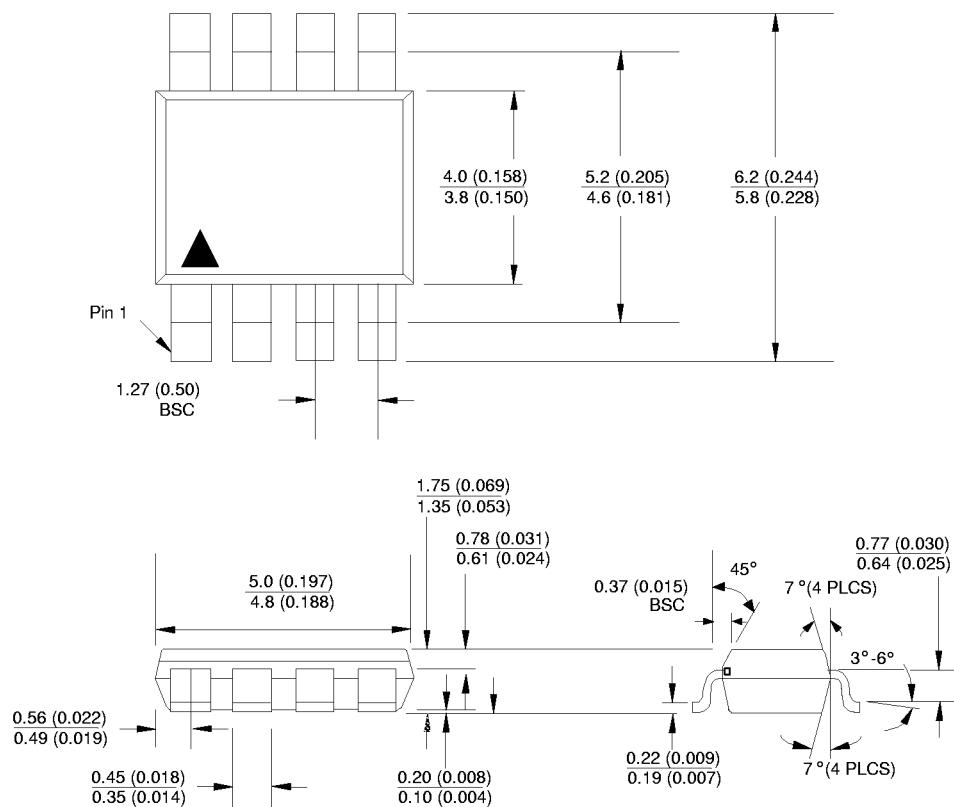
Figure 1c. Test Circuit 3

TYPICAL APPLICATIONS

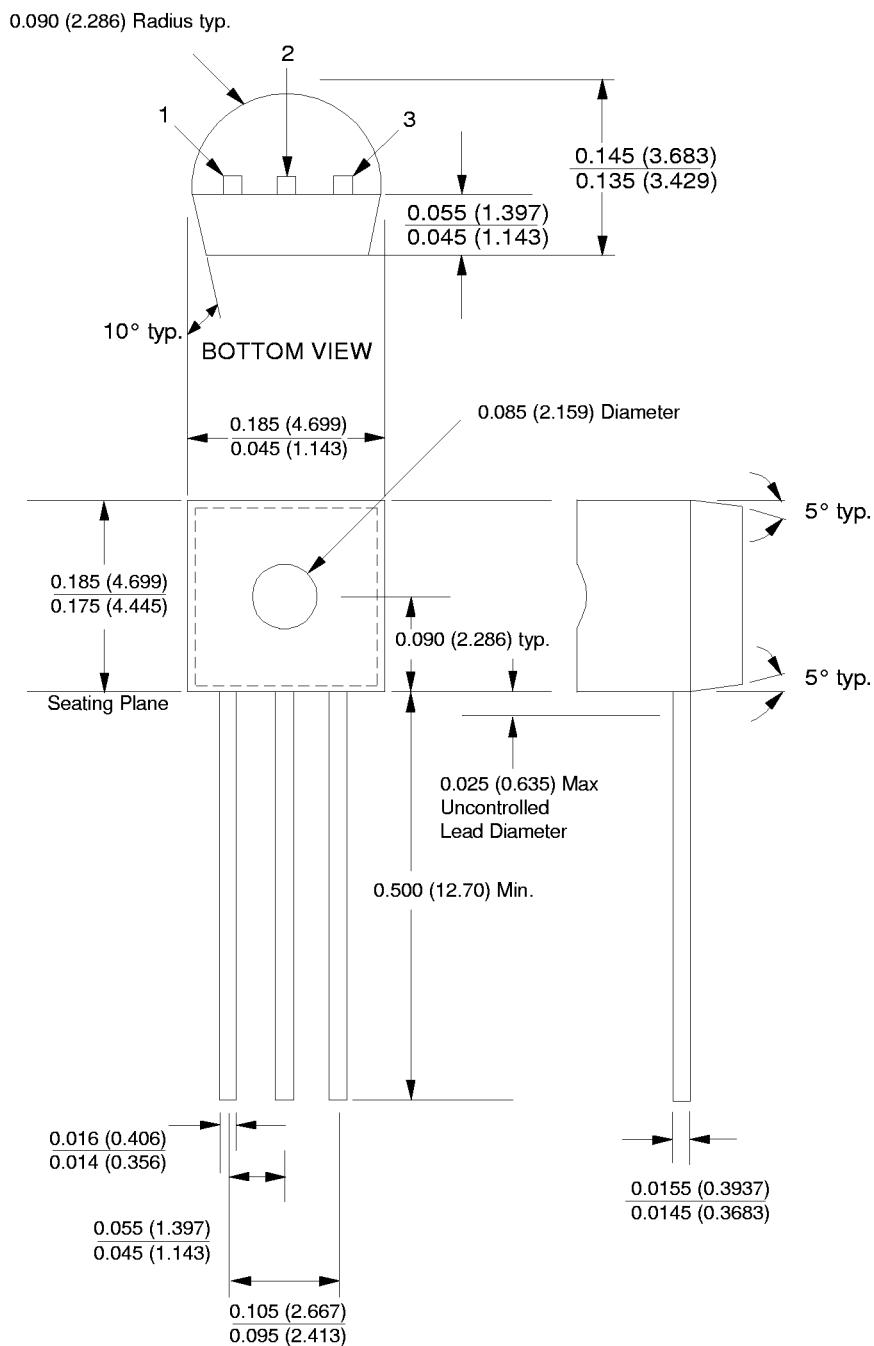


*If the output voltage has noise, then please add a $0.1\mu\text{F}$ in between drain and gate of power MOSFET to reduce the noise.

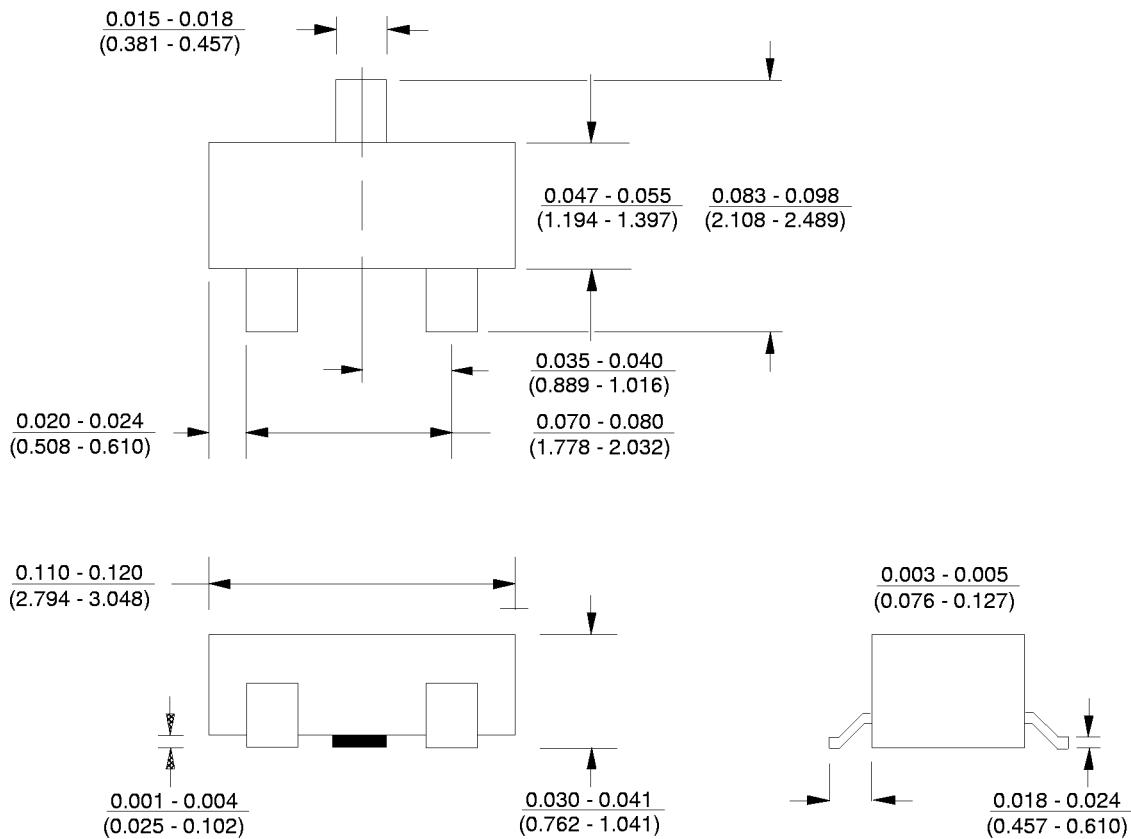
PACKAGE DRAWING
SOIC-8 (S)



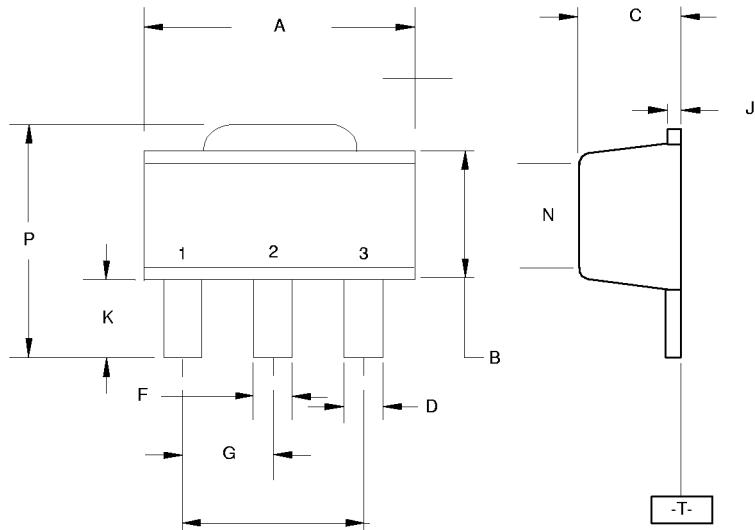
PACKAGE DRAWING
TO-92 (N)



PACKAGE DRAWING
SOT-23-3L (M)



PACKAGE DRAWING
SOT-89 (M1)

**STYLE 1**

- PIN 1. BASE
- 2. COLLECTOR
- 3. Emitter

STYLE 3

- PIN 1. GATE
- 2. ANODE
- 3. CATHODE

STYLE 2

- PIN 1. ANODE
- 2. CATHODE
- 3. NO CONNECTION

STYLE 4

- PIN 1. DRAIN
- 2. GATE
- 3. SOURCE

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.40	4.60	0.174	0.181
B	2.29	2.60	0.091	0.102
C	140	160	0.056	0.062
D	0.36	0.48	0.015	0.018
E	1.62	1.80	0.064	0.070
F	0.44	0.53	0.018	0.020
G	150 BSC		0.059 BSC	
J	0.35	0.44	0.014	0.017
K	0.80	1.04	0.032	0.040
L	300 BSC		0.118 BSC	
N	2.04	2.28	0.081	0.089
P	3.94	4.25	0.156	0.167